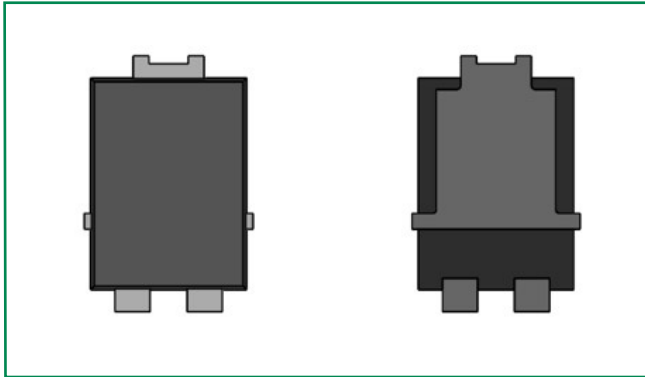
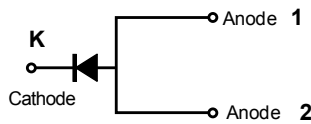


DST2080S



Pin out



Description

Littelfuse DST series Ultra Low V_F Schottky Barrier Rectifier is designed to meet the general requirements of commercial and industry applications by providing high temperature, low leakage and lower V_F products.

It is suitable for high frequency switching mode power supply, free-wheeling diodes and polarity protection diodes.

Features

- Ultra low forward voltage drop
- High frequency operation
- MSL: Level 1 - unlimited
- High junction temperature capability
- Trench MOS Schottky technology
- Single die in TO-277B Package
- Pb-free E3 means 2nd level interconnect is Pb-free and the terminal finish material is tin(Sn) (IPC/ JEDEC J-STD-609A.01)

Applications

- Switching mode power supply
- DC/DC converters
- Free-Wheeling diodes
- Polarity Protection Diodes

Maximum Ratings

Parameters	Symbol	Test Conditions	Max	Unit
Peak Inverse Voltage	V_{RWM}	-	80	V
Average Forward Current (per device) *	$I_{F(AV)}$	50% duty cycle @ $T_A = 85^\circ\text{C}$ rectangular wave form	20	A
Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	150	A

* Mounted on 30 mm x 30 mm pad areas aluminum PCB

Electrical Characteristics

Parameters	Symbol	Test Conditions	Typ	Max	Unit
Forward Voltage Drop (per leg) *	V_{F1}	@10A, Pulse, $T_J = 25^\circ\text{C}$	0.52	-	V
		@20A, Pulse, $T_J = 25^\circ\text{C}$	0.64	0.70	
	V_{F2}	@10A, Pulse, $T_J = 125^\circ\text{C}$	0.46	-	
		@20A, Pulse, $T_J = 125^\circ\text{C}$	0.60	0.65	
Reverse Current (per leg) *	I_{R1}	@ $V_R = \text{rated } V_R, T_J = 25^\circ\text{C}$	22	300	μA
	I_{R2}	@ $V_R = \text{rated } V_R, T_J = 125^\circ\text{C}$	11	75	mA

* Pulse Width < 300 μs , Duty Cycle < 2%

Thermal-Mechanical Specifications

Parameters	Symbol	Test Conditions	Max	Unit
Junction Temperature	T_J		-55 to +150	°C
Storage Temperature	T_{stg}		-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	$R_{th,JA}$	DC operation	70	°C/W
Approximate Weight	wt		0.08	g
Case Style		TO-277B		

Figure 1: Typical Forward Characteristics

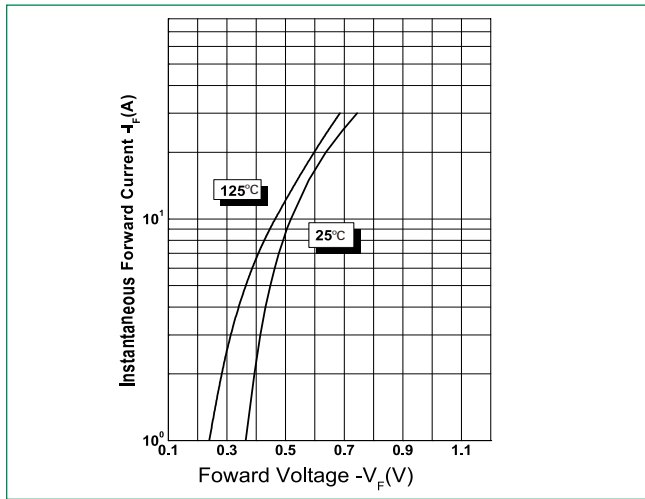


Figure 2: Typical Reverse Characteristics

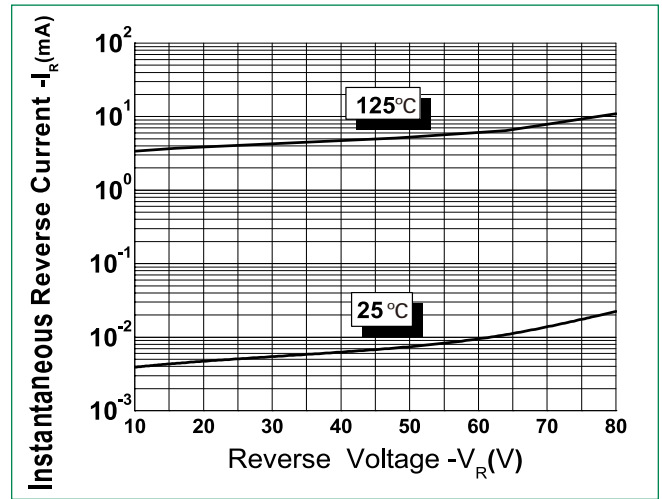


Figure 3: Typical Junction Capacitance

